



DCR890F65

Phase Control Thyristor

Replaces DS5924-4 DS5924-5 December 2023 (LN42952)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to 125°C,
DCR890F65*	6500	IDRM = IRRM = 200mA,
DCR890F60	6000	VDRM, VRRM tp = 10ms
DCR890F55	5500	VDSM & VRSM =
DCR890F50	5000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR890F65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

VDRM 6500V
Iτ(AV) 910A
Iτsm 12000A
dV/dt* 1500V/μs
dI/dt 200A/μs

^{*}Higher dV/dt selections are available on request

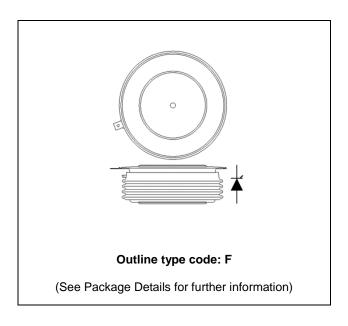


Fig. 1 Package outline

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^{*6200}V @ -40°C, 6500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	910	А
IT(RMS)	RMS value	-	1430	А
lτ	Continuous (direct) on-state current	-	1410	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	12.0	kA
l²t	I2t for fusing	V _R = 0	0.72	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	18.3	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cinale side socied	Anode DC	-	33.3	°C/kW
		Single side cooled	Cathode DC	-	41.7	°C/kW
D	Thermal resistance - case to heatsink	Clamping force 23kN (with mounting compound)	Double side	-	4.0	°C/kW
Rth(c-h)			Single side	-	8.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			20	25	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	200	mA
V тм	Instantaneous forward voltage	At 2900A peak, T _j = 25°C		2.70	3.10	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% VDRM, Tj = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	100	A/µs
		tr < 0.5µs, Tj = 125°C	Non-repetitive	-	200	A/µs
.,	Threshold voltage - Low level	300A to 1000A at Tcase = 1	25°C	-	1.01	V
V т(то)	Threshold voltage - High level	1000A to 3500A at Tcase = 125°C		-	1.19	V
_	On-state slope resistance - Low level	300A to 1000A at Tcase = 125°C		-	1.13	mΩ
ľτ	On-state slope resistance - High level	1000A to 3500A at Tcase = 125°C		-	0.95	mΩ
t gd	Delay time	$V_D = 67\% \ V_{DRM}, \ gate \ source \ 30V, \ 10\Omega$ $t_T = 0.5 \mu s, \ T_j = 25 ^{\circ} C$		-	3	μs
tq	Turn-off time	Tj = 125°C, Ipeak = 1000A, tp = 1000μs, VR = 100V, dI/dt = 5A/μs, dVpR/dt = 20V/μs linear to 2500V		600	1000	μs
Qs	Stored charge	T _j = 125°C, dl/dt = 1A/μs,		2150	3760	μC
IRR	Reverse recovery current	VR peak ~ 3900V, VR ~ 2450V		36	46	А
Qs	Stored charge	I _T = 1000A, t _P = 1000μs, T _j = 125°C, dI/dt = 5A/μs, V _R peak = 100V. [LEM]		2500	4000	μC
IRR	Reverse recovery current			90	120	А
I L	Latching current	Tj = 25°C, VD = 5V		-	3	А
Ін	Holding current	Tj = 25°C, Rg-κ = ∞, Iтм = 500A, Iт = 5A		-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
IGD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

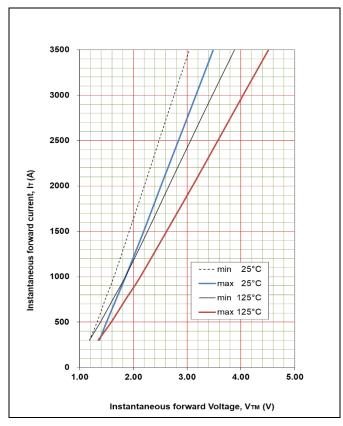


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.625719

B = 0.057113

C = 0.000832

D = 0.008411

These values are valid for T_j = 125°C for I_T 300A to 3500A

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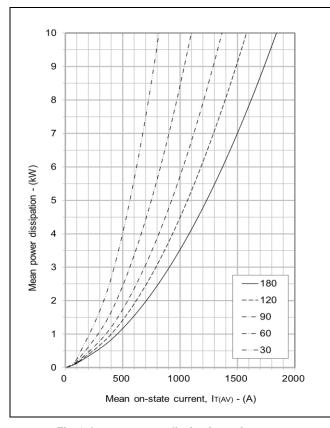


Fig. 3 On-state power dissipation - sine wave

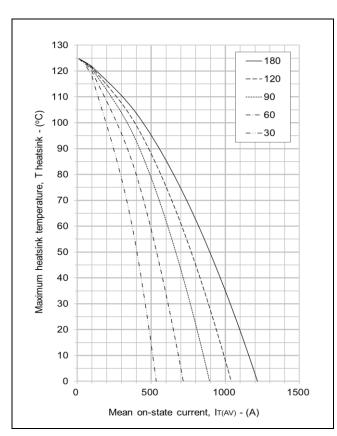


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

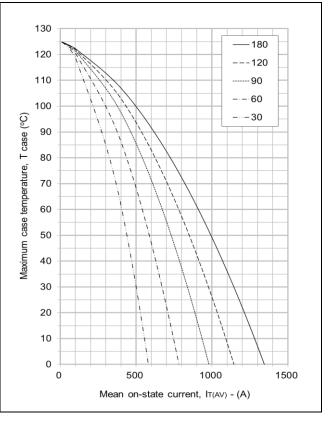


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

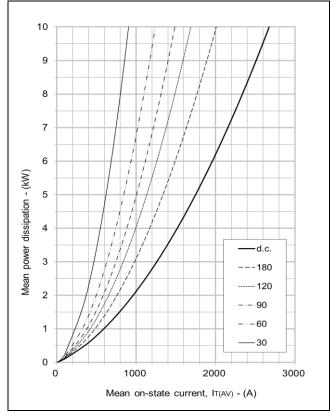


Fig. 6 On-state power dissipation - rectangular wave

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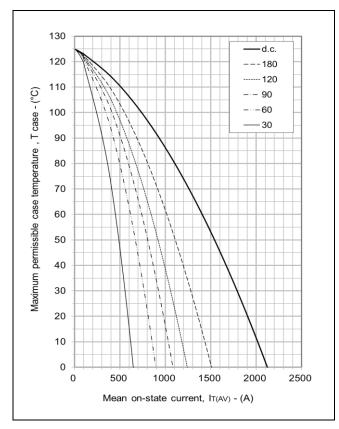
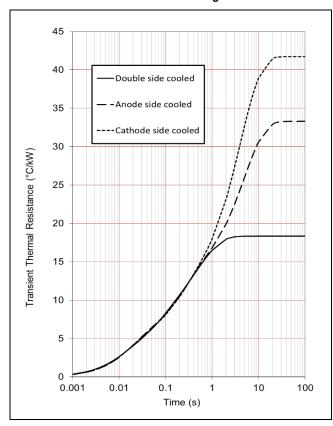


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



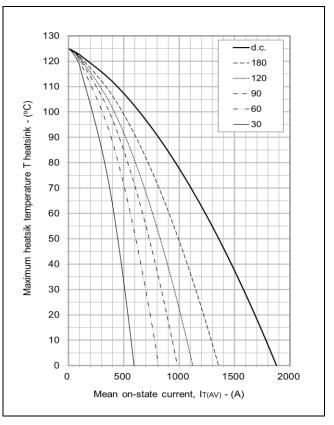


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	7.561	4.077	3.842	2.867
cooled	Ti(s)	0.688	0.254	0.061	0.010
Anode side cooled	Ri(°C/kW)	11.556	8.581	4.794	8.364
	Ti(s)	4.222	6.027	0.017	0.226
Cathode side	Ri(°C/kW)	6.721	4.622	15.539	14.863
cooled	Ti(s)	0.191	0.016	5.001	3.317

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

	Double side cooling						
	ΔZ_{th} ((z)					
6°	sine.	rect.					
180	3.19	2.14					
120	3.72	3.10					
90	4.29	3.64					
60	4.81	4.23					
30	5.22	4.88					
15	5.40	5.22					

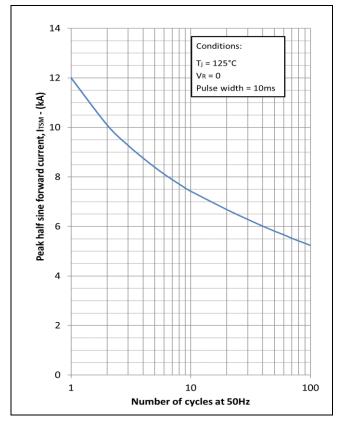
ouble side cooling			Anode Side Cooling		
$\Delta Z_{th}(z)$				_h (z)	
sine.	rect.		θ°	sine.	rect.
3.19	2.14		180	2.97	203
3.72	3.10		120	3.43	289
4.29	3.64		90	3.92	3.36
4.81	4.23		600	4.36	3.87
5.22	4.88		30	4.69	4.41
5 40	522		15	4.84	4.70

C d	umeam	a Cooling				
	$\Delta Z_{th}(z)$					
θ°	sine.	rect.				
180	295	2.02				
120	3.40	2.87				
90	3.88	3.34				
60	4.31	3.84				
30	4.64	4.37				
15	479	465				

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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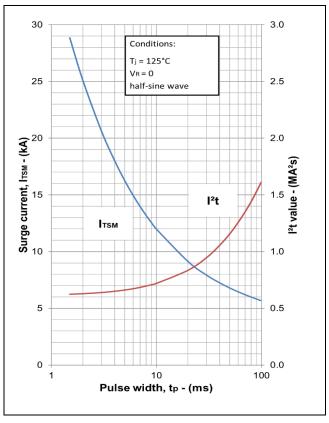


Fig. 10 Multi-cycle surge current

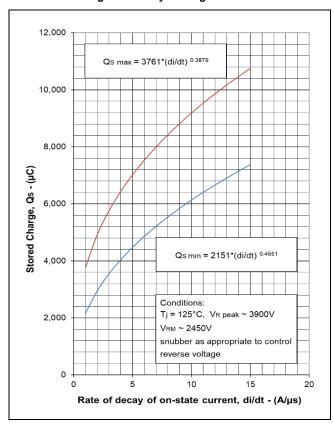


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

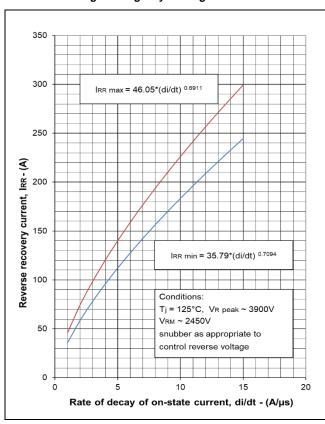


Fig. 13 Reverse recovery current

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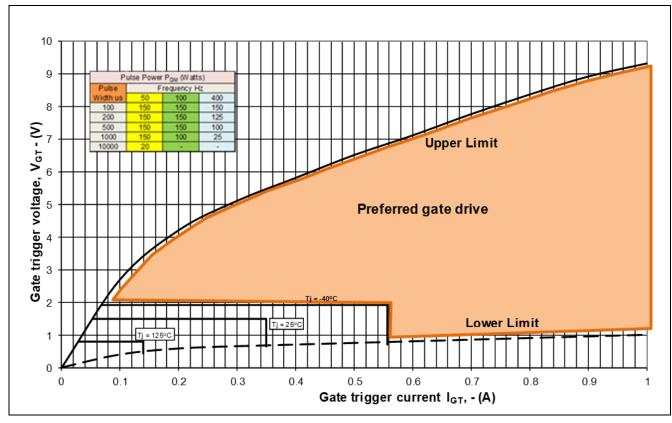


Fig. 14 Gate characteristics

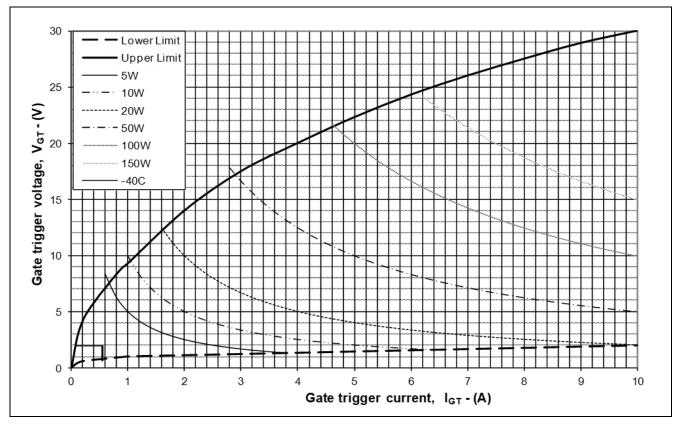


Fig. 15 Gate characteristics

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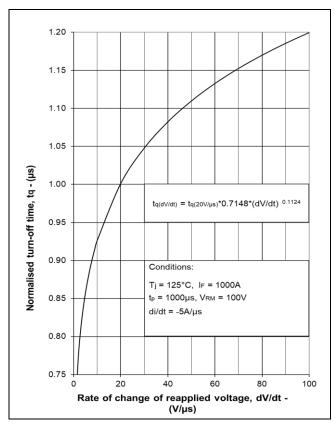


Fig. 16 Turn-off time

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

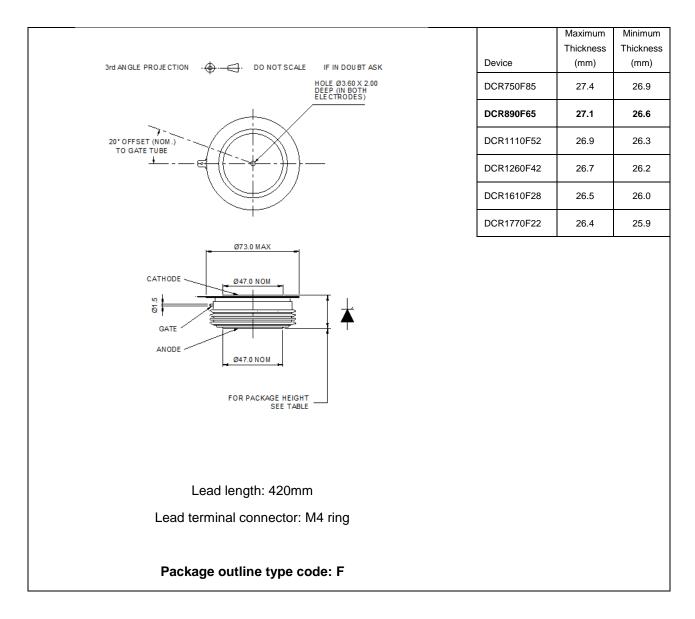


Fig. 17 Package outline

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